2N2907

TO-92 Plastic-Encapsulate Transistors

FEATURES

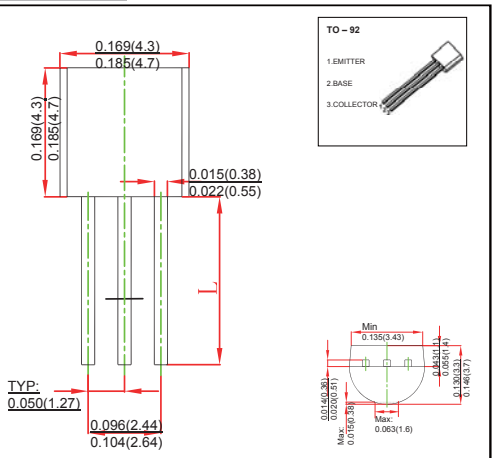
●PNP TRANSISTOR

MECHANICAL DATA

●Case style:TO-92 molded plastic

●Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.6	A
P_C	Collector Dissipation	0.625	W
T_J	Junction Temperature	150	˚C
T_{stg}	Storage Temperature	-55~+150	˚C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10uA, I_E = 0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1 0 m A , I_B = 0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10 μA, I_C = 0	- 5			V
Collector cutoff current	I_{CBO}	V_{CB} = -50 V, I_E = 0			-10	nA
Emitter cutoff current	I_{EBO}	V_{EB} = - 3 . 0 V , I_C = 0			-10	nA
DC current gain	h_{FE}	IC =-0.1mA, VCE =-10V	52			
		IC =-150mA, VCE = -10 V	100		300	
		IC =-500mA, VCE =-10V	3 2			
Collector-emitter saturation voltage	$V_{CE(sat)}$	IC =-150mA, IB =-15 mA			-0.4	V
		IC =-500mA, IB =-50 mA			-0.67	
Base-emitter saturation voltage	$V_{BE(sat)}$	IC =-150mA, IB =-15mA			-1.0	V
		I_C =-500 mA, I_B = - 5 0 m A			-1.2	
Transiston frequency	f_T	V_{CE}=-20V,I_C=-50mA,f=100MHz	200			MHz
Delay time	Td	Vcc=-30V,			10	ns
Rise time	Tr	IC=-150mA.I_{B1}=-15mA			25	ns
Storage time	Ts	V_{CC}=-6V,IC=-150mA			225	ns
Fall time	Tf	IB1=IB2=-15mA			60	ns

CLASSIFICATION OF $h_{FE(2)}$

Rank	L	H
Range	100-200	200-300

RATINGS AND CHARACTERISTIC CURVES

Typical Characterisitics